Abstract of the Disclosure

A method for fabricating a semiconductor device capable of preventing an electric short circuit between a storage node contact plug and a conductive pattern by forming an attack barrier layer or use of an insulation layer having a flow-fill property. The attack barrier layer for preventing the electric short circuit is formed by employing two methods. First, the attack barrier layer is formed on an entire surface of a structure containing the plugs after the CMP process and the cleaning process. Second, the attack barrier layer is formed on a structure including a storage node contact hole such that the attack barrier layer fills the lost portion of the insulating material-based layer. Also, instead of using the attack barrier layer, the insulation layer having a flow-fill property is deposited after the cleaning process.